

Vishay Siliconix

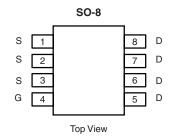
# N-Channel 2.5-V (G-S) MOSFET

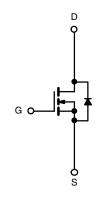
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)		
20	0.009 at V <sub>GS</sub> = 4.5 V	13.5		
	0.013 at V <sub>GS</sub> = 2.5 V	11		

#### FEATURES

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC







N-Channel MOSFET

Ordering Information: Si4466DY-T1-E3 (Lead (Pb)-free) Si4466DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25 \degree C$ , unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	20		V	
Gate-Source Voltage		V <sub>GS</sub>	± 12			
	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	13.5	9.5	٨	
Continuous Drain Current $(T_J = 150 \ ^{\circ}C)^a$	T <sub>A</sub> = 70 °C		10.5	7.5		
Pulsed Drain Current		I <sub>DM</sub>	50		A	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	2.7	1.36		
	T <sub>A</sub> = 25 °C	– P <sub>D</sub>	3.0	1.5	w	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		1.9	0.95		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 s	- R <sub>thJA</sub> R <sub>thJF</sub>	33	42	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		70	84	
Maximum Junction-to-Foot (Drain)	Steady State		16	21	

Notes:

a. Surface Mounted on FR4 board, t  $\leq$  10 s.

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<b>MOSFET SPECIFICATIONS</b> $T_J = 25 ^{\circ}C$ , unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.6	1.0	1.4	V			
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 100	nA			
Zero Gate Voltage Drain Current	lago	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1	μA			
	IDSS	$V_{DS}$ = 20 V, $V_{GS}$ = 0 V, $T_{J}$ = 55 °C	T <sub>J</sub> = 55 °C		5				
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5$ V, $V_{GS}$ = 4.5 V	30			Α			
	B	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 13.5 A		0.0055	0.009	Ω			
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 11 A		0.0078	0.013				
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 13.5 \text{ A}$		70		S			
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{\rm S}$ = 2.7 A, $V_{\rm GS}$ = 0 V		0.70	1.1	V			
Dynamic <sup>b</sup>									
Gate Charge	Qg			40	60				
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 4.5 V, $I_{D}$ = 13.5 A		7		nC			
Gate-Drain Charge	Q <sub>gd</sub>			12					
Gate Resistance	Rg		0.5	1.9	3.3	Ω			
Turn-On Delay Time	t <sub>d(on)</sub>			20	30				
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$		15	25				
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 $\Omega$		150	250	ns			
Fall Time	t <sub>f</sub>			70	110	1			
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.7 A, dI/dt = 100 A/μs		55	90	1			

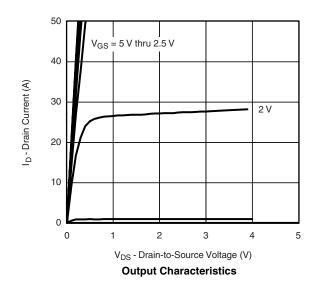
Notes:

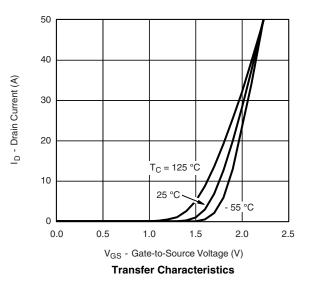
a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

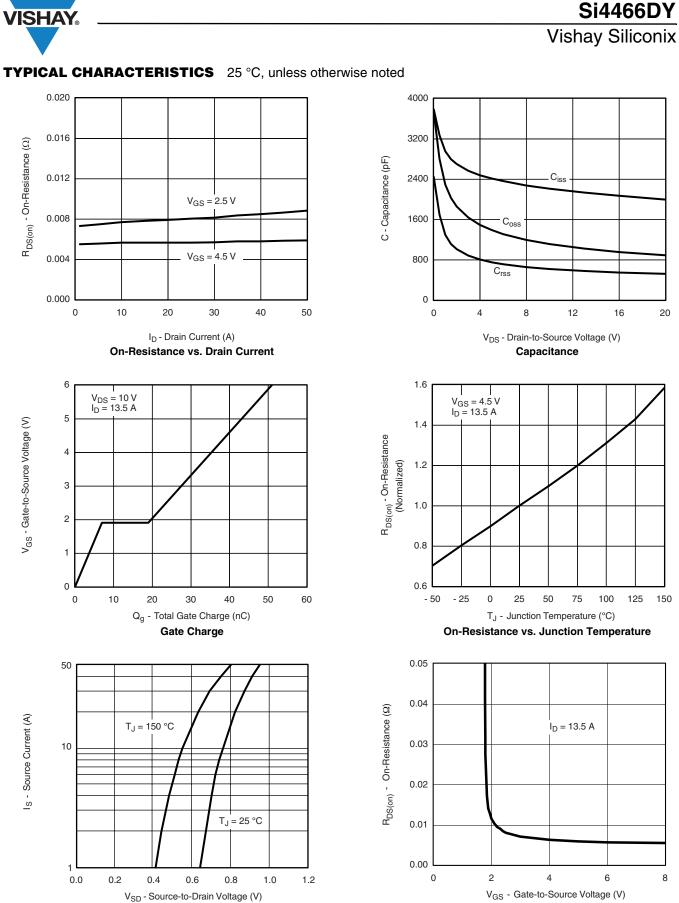
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







Source-Drain Diode Forward Voltage

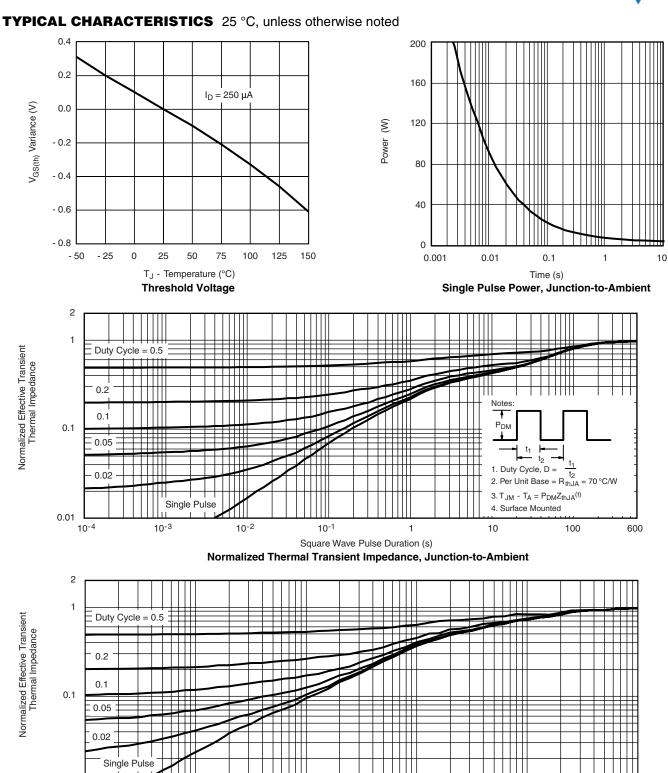
Document Number: 71820 S09-0767-Rev. F, 04-May-09 **On-Resistance vs. Gate-to-Source Voltage** 

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## Si4466DY

### **Vishay Siliconix**



Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Foot

10-1

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?71820">www.vishay.com/ppg?71820</a>.

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0.01

10<sup>-3</sup>

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